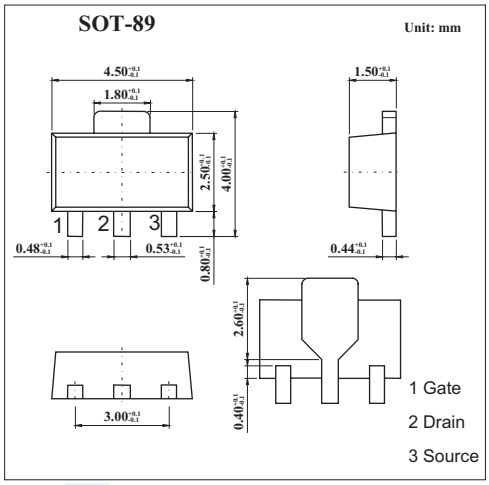
Silicon N-Channel MOSFET
2SK3065



■ Features

- Low on resistance.
- High-speed switching.
- Optimum for a pocket resource etc. because of undervoltage actuation (2.5V actuation).
- Driving circuit is easy.
- Easy to use parallel.

  It is strong to an electrostatic discharge.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	2	A
	I_{dp} *	8	A
Power dissipation Tc=25℃	P_D	0.5	W
Channel temperature	T_{ch}	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW≤10μs,Duty Cycle≤1%

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain to source breakdown voltage	V_{DSS}	I_D=1mA,V_{GS}=0	60			V
Drain cut-off current	I_{DSS}	V_{DS}=60V,V_{GS}=0			10	μA
Gate leakage current	I_{GSS}	V_{GS}=±20V,V_{DS}=0			±10	μA
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=10V,I_D=1mA	0.8		1.5	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS}=10V,I_D=1A	1.5			S
Drain to source on-state resistance	$R_{DS(on)}$	V_{GS}=4V,I_D=1A		0.25	0.32	Ω
		V_{GS}=2.5V,I_D=1A		0.35	0.45	Ω
Input capacitance	C_{iss}	V_{DS}=10V,V_{GS}=0,f=1MHZ		160		pF
Output capacitance	C_{oss}			85		pF
Reverse transfer capacitance	C_{rss}			25		pF
Turn-on delay time	t_{on}	I_D=1A,$V_{GS(on)}$=4V,R_L=30Ω,V_{DD}=30V,R_G=10Ω		20		ns
Rise time	t_r			50		ns
Turn-off delay time	t_{off}			120		ns
Fall time	t_f			70		ns

■ Marking

Marking	KE